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Investigation and Analysis of On-Chip ESD Protection Circuit under Electromagnetic Pulse

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Abstract: The electrostatic discharge (ESD) protection circuit widely exists in the input and output ports of CMOS digital circuits, and electromagnetic pulse coupled into the device not only interacts with the CMOS circuit, but also acts on the protection circuit. This paper establishes on-chip electrostatic discharge protection circuit model, and draws the lattice temperature, current density and electric field intensity distribution from the multi-physical parameter model to explore the changes of the internal devices when the pulse comes. The results show that the ESD protection circuit has potential damage risk, and the injection of EMP leads to irreversible heat loss inside the circuit. In addition, pulse signals with different attributes will change the damage threshold of the circuit. These results provide an important reference for further evaluation of the influence of electromagnetic environment on the chip, which is helpful to carry out the reliability enhancement research of ESD protection circuit.

Key words: Damage effect, damage location prediction, electromagnetic pulse (EMP), on–chip ESD protection circuit.

1. Introduction

The threat of electromagnetic pulse(EMP) to electronic system drives the research of electromagnetic effect. The vulnerability of electronic system to EMP is the fatal weakness of important civil infrastructure. With the development of technology in the direction of smaller and faster, the possibility of microwave energy destroying electronic systems is also increasing[1-3]. When the circuit system is in a complex electromagnetic environment, the electromagnetic interference (EMI) phenomenon is a typical reliability problem, which can easily enter the system through the coupling of the front door or the back door[4-6].CMOS technology plays a dominant role in digital circuits. In addition, electrostatic discharge (ESD) protection circuits are widely used in the input and output ports of CMOS digital circuits[7]. They are relatively independent of the buffer circuit and logic circuit of the device, the electromagnetic pulse coupled into the device interacts with the CMOS circuit and does not exclude the ESD protection circuit. The results show that the ESD protection circuit plays an important role when the EMP comes[8, 9]. During the 1991 Gulf War, a large number of Iran military equipment suddenly failed, and in the 2003 Iraq War, the United States used electromagnetic bombs to paralyze national television broadcasting system of Iraq. These two incidents tell us that even if the overall electronic equipment is not destroyed, its internal equipment has accidentally failed[10, 11].

On-chip ESD protection circuit is an essential part of integrated circuits in CMOS chips. In order to obtain an efficient CMOS ESD protection circuit, the use of resistors and diodes has been gradually changed to the use of three-layer devices, such as MOSFET and parasitic n-p-n or p-n-p bipolar junction transistors (BJT) in CMOS technologies. If properly designed and optimized, a parasitic four-layer silicon-controlled rectifier (SCR) structure is used to effectively protect the chip

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from ESD damage[12, 13]. Diode-triggered silicon-controlled rectifier (DTSCR) has the characteristics of snapback I-V behavior, low parasitic capacitance, high ESD current handling capability and small size[14, 15], which is a robust ESD protection device and has become the main electrostatic discharge protection component used in nano-scale processes. For low power consumption and high speed circuit design requirements, STI-DTSCR has obvious low leakage current and can provide ESD protection[16]. At present, the research on ESD is mainly through the SPICE model to explore the influence of electrostatic discharge on circuit performance and optimize the device. M. D. Ker et al. proposed a novel NANSCR to protect the ultra-thin gate oxide of the input stage from ESD stress[17]. J. H. Lee et al. proposed a two-level trigger scheme to realize the ESD protection device of nanotechnology[18]. G. Hiblot et al. studied the sensitivity of latch-up effect to wafer thickness by using TCAD software and C. Li et al. further built a three-dimensional device model[19, 20].

This paper builds a CMOS electrostatic discharge protection circuits which adopts DTSCR as ESD circuit module with multiple physical parameter. Since the constructed DTSCR has a holding voltage which less than 1.1 V, ESD protection circuit can be applied to more advanced process design. Compared with the previously established SPICE model, this paper is not limited to the circuit level and draws the lattice temperature, current density, and electric field intensity distribution of the internal device. At the same time, the transient simulation is carried out to simulate the discharge path of PS and ND modes under positive and negative EMP pulses. And the damage prediction and reliability analysis of ESD protection circuit are discussed in the case of pulse injection. The organization of this paper is as follows. In the second section, with CMOS inverter as the starting point, the equivalent numerical model of CMOS circuit with ESD protection is constructed by combining physical model and geometric model. In the third section, the transient response of the input and output ports under EMP injection is studied from both electrical and thermal aspects, and the temperature distribution and high temperature hot spot area inside the device are explored under positive and negative pulses. The fourth section gives the influence of microwave parameter changes on the internal temperature of the device, which helps to predict the damage area of the device and perform reliability reinforcement.

2. Methodology

2.1. Device structure

In this paper, the ESD-protected CMOS circuit is taken as the research object, and the traditional diode-triggered silicon-controlled rectifier model and the CMOS inverter model are constructed. In the specific simulation process, the Sentaurus TCAD is used to simulate the two-dimensional physical structure of the DTSCR device. The structure diagram is shown in Fig. 1.

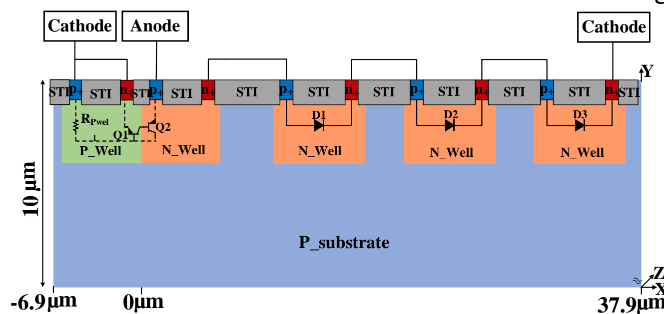

Fig. 1. Device model of DTSCR.

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From top to bottom, there is an active region of 80 nm, a well depth of 4 um, and a P-type doped substrate of 10 um. And the STI shallow trench isolation method is used[21]. The whole device model is 44.8 μm long and 10 μm wide. The substrate, P-well and N-well are lightly doped, and the active region is heavily doped with a Gaussian distribution. The doping concentrations are 1×10^{15} cm^{-3},7×10^{16} cm^{-3},1×10^{15} cm^{-3}, respectively.

In order to ensure the basic working principle of the CMOS inverter, the CMOS two-dimensional device model is constructed from the classical theoretical model as shown in Fig. 2[22]. The device model consists of NMOS in the P-type substrate and PMOS in the N-well. The distance between the gates in the NMOS and PMOS regions is 5 μm, the gate length is 0.35 μm, the device length is 14.35 μm, and the width is 4 μm. The source and drain regions are heavily doped by Gaussian distribution. In addition, the initial temperature of the two devices is set to 300 K, and the lattice temperature of the hot electrode at the bottom of the device is fixed at 300 K.

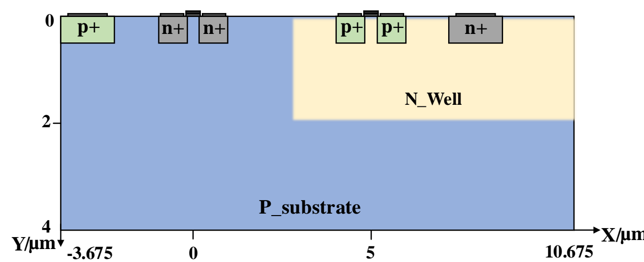

Fig. 2. Device model of CMOS inverter.

2.2. Circuit model

The circuit model is shown in Fig. 3. An on-chip ESD protection circuit consists of two DTSCR device models and an inverter TCAD device model[23]. The traditional DTSCR device cross-sectional view of DTSCR is shown in Fig. 3.

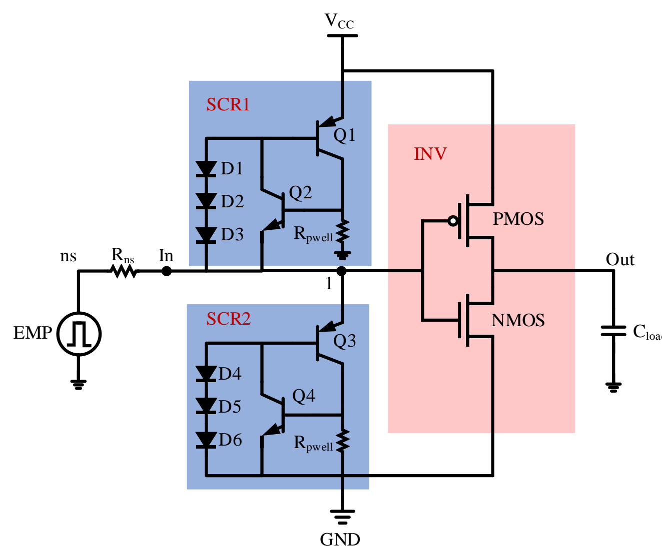

Fig. 3. On-chip ESD protection circuit.

The DTSCR device is basically formed by the parasitic lateral n-p-n bipolar junction transistor (BJT) Q1 and parasitic vertical p-n-p BJT Q2. The emitter, base and collector of Q1 are composed of

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n+ / P_Well / N_Well, and the collector, base and emitter of Q2 are composed of P_Well / N_Well / p+[24]. The SCRl device is arranged between 1V VCC and “In” with its anode connected to VCC. The SCR2 device is arranged between “In” and 0V GND with its anode connected to “In”. The cathode of SCR1, the anode of SCR2 and the gate input “In”, and Rns is regarded as the internal resistance of the signal source. The drain of NMOS and PMOS is connected “Out”, which is connected to GND through a large capacitance Cload. Since the current of the silicon-controlled rectifier always flows from the anode to cathode, the SCR device can only be used for unidirectional ESD input. When the positive pulse signal acts on the input port, since the pulse signal has a positive voltage with respect to the GND node, the discharge path in the PS mode is turned on, so SCR2 is turned on. When the negative pulse signal comes, VCC has a positive voltage with respect to the In node, and the device SCR1 is turned on in the ND discharge mode.

2.3. Physical model

In the process of high power electromagnetic pulse injection, the temperature of the device will rise for a period of time. To describe the electrothermal model of the two-dimensional device more accurately, the thermodynamic model is needed to simulate the transport of carriers in the process of TCAD simulation[25]. In this paper, the electrothermal effect is taken into account, and the non-isothermal model is adopted. It is assumed that the carrier and the lattice are in a thermodynamic equilibrium state to improve the accuracy of the simulation calculation. In this thermodynamic model, Poisson equation, current density equation and heat conduction equation need to be solved. The Poisson equation can be expressed as below.

$$\nabla^2\Psi = -\frac{q}{\varepsilon}(p - n + N_D^+ - N_A^-) \tag{1}$$

Among them, ε is the capacitance, q is the basic charge, n and p represent the electron and hole density, N_D^+ and N_A^- represent the ionized donor and ionized acceptor concentration respectively. In addition, the temperature gradient of the semiconductor will also affect the movement of the carrier, so it is necessary to consider the influence of the internal temperature gradient caused by the self-heating effect on the carrier transport[26]. The modified current density equation of electrons and holes can be expressed as below.

$$J_n = -nqu_n(\nabla\phi_n + P_n\nabla T) \tag{2}$$

$$J_p = -pqu_p(\nabla\phi_p + P_p\nabla T) \tag{3}$$

where u_n and u_p are the carrier mobility, Φ is the quasi-Fermi potential of the carrier, and P is the absolute thermoelectric power of the carrier. In the thermodynamic model, the temperature T is represented by an equation related to the lattice temperature.

$$\begin{aligned} c\frac{\partial T}{\partial t} - \nabla\kappa\nabla T = -\nabla[(P_nT+\phi_n)J_n + (P_pT+\phi_p)J_p] - \\ \left(E_C + \frac{3}{2}k_BT\right)\nabla J_n - \left(E_V - \frac{3}{2}k_BT\right)\nabla J_p + qR(E_C - E_V + 3k_BT) \end{aligned} \tag{4}$$

In the formula, c represents the lattice heat capacity, κ is the thermal conductivity of the material, and kB is the Boltzmann constant. EC and EV represent the conduction band and valence band energy levels, respectively.

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3. Result and discussion

3.1. Simulation analysis of the model

Combined with the above physical model and geometric model, the circuit model is simulated in two dimensions from the electrical characteristics and thermal characteristics respectively. The IV characteristics of diode-triggered silicon-controlled rectifier are shown in Fig.4.The trigger voltage of the DTSCR model is 3.3 V, which is about the conduction voltage of four series diodes, and the maintenance voltage is 1.1 V.

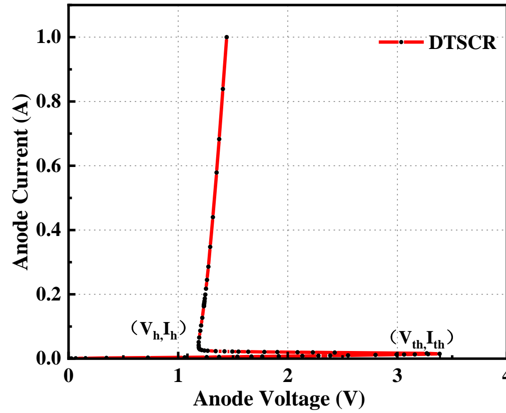

Fig. 4. The IV characteristics of DTSCR.

Fig.5 shows the current and voltage transmission characteristics of the two-dimensional CMOS inverter at 1 V driving voltage. It can be seen that the turn threshold of the device is about 0.54 V, the VOH is about 0.95 V, and the VOL is about 0.07 V.

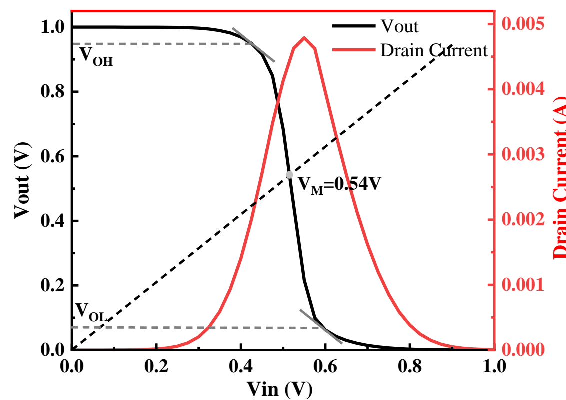

Fig. 5. Basic characteristics of CMOS inverter.

In order to simulate the damage effect of EMP pulse on ESD protection circuit, the square wave voltage signal is selected as the pulse model, which has been proved to be equivalent to EMP[27]. In Fig. 3, a voltage source signal and a resistor Rns are used to generate a negative square wave signal. In this paper, the rise time and amplitude of the square wave signal are set to 1 ns and 20 V respectively, and the pulse width of the signal is 14 ns. The pulse signal is injected into the input port "In", and the response of the EMP pulse to the circuit model is analyzed by observing the changes of voltage and current in the circuit. As shown in Fig. 6(a), when the negative pulse signal is injected at 1 ns, since the input resistance of port "In" is much larger than Rns, the ESD protection circuit module does not start, so that the input voltage Vin will increase sharply with the injection of the pulse signal. When the voltage difference between the two ends of the DTSCR device reaches its

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trigger voltage, the ESD protection circuit starts, and a large current discharge path is formed. As shown in Fig. 6(b), due to the injection of negative pulses, the input signal with negative voltage polarity to VCC and the discharge path of the ND mode is turned on, making the device SCR1 the main current leakage branch. The current ISCR1 flowing through SCR1 is approximately equal to the input current I_{in}. The ISCR1 reaches stability at 3ns, and the input voltage Vin also decreases from the peak value to stable value. Since ISCR2 is close to zero, so SCR1 plays a major role in the negative EMP injection process. Due to the existence of the gate capacitance of the CMOS inverter[28], IINV will change with Vin. During the change of Vin, Vout is always at 1 V, indicating that the inverter and the ESD protection circuit module works stably.

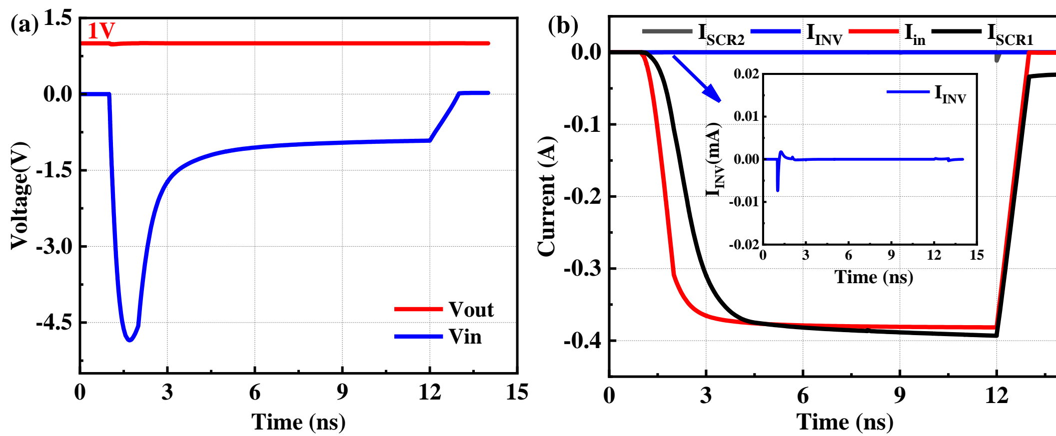

Fig. 6. Transient signals of voltage and current. (a) The change of voltage with time. (b) The change of current with time

3.2. The damage effect and mechanism analysis

In order to analyze the influence of microwave pulse EMP injection on the device in the circuit, the positive and negative square wave signals with an amplitude of 400 V are taken as an example to analyze the heating process inside the device under EMP. Fig. 7 shows the temperature changes inside each device during the injection of negative pulse signals.

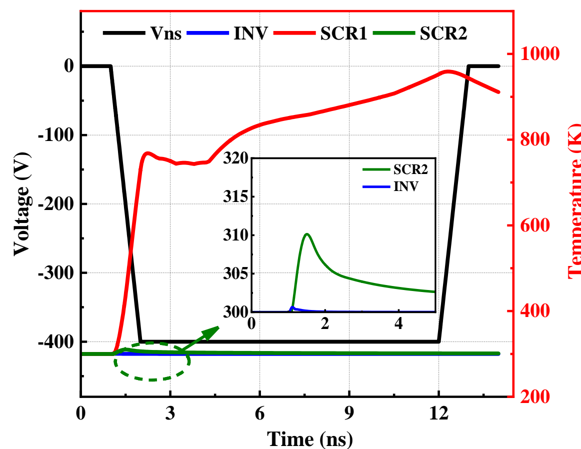

Fig. 7. The variation of the peak temperature of the device with time under negative pulse.

As the negative EMP pulse signal is injected into the circuit, the device SCR1 will flow through a large amount of discharge current, resulting in a large amount of Joule heat inside the device, and the peak temperature of SCR1 rises, which may cause damage to the device, while the peak temperature inside the CMOS inverter only fluctuates slightly when the signal is injected. The mechanism of thermal damage caused by EMP on the device is further studied by observing the

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temperature distribution inside the device under positive and negative pulses. In Fig. 8(a), during the process of simulating the negative pulse signal, it is determined that SCR1 is prone to burn out, and is observed that the negative polarity signal has a great influence on the SCR1, and there is a high temperature area represented by red. The hot spot is located in the main SCR path composed of n+/ P_well / N_well / p+ in the device, and there is no obvious hot spot in the SCR2 and CMOS inverter.

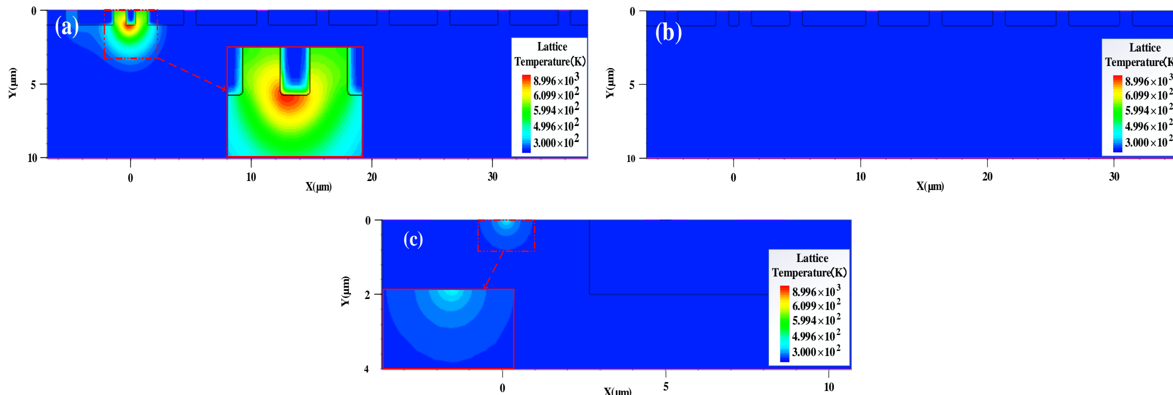

Fig. 8. Internal temperature distribution of the device under negative pulse. (a) Temperature distribution of SCR1. (b) Temperature distribution of SCR2. (c) Temperature distribution of CMOS inverter.

Fig. 9 shows the total current density, electric field intensity and mobility distribution of SCR1 under negative pulse. In Fig. 9(a) and (b), it can be seen that the maximum area of current density distribution is located on the main SCR path, and that of electric field intensity is located in the corner of the active area. These results show that the corner of the active area on the main SCR path is the weakest part due to the heat accumulation effect, which is consistent with the hot spot position in Fig. 8(a). The increase of temperature will reduce the mobility of carriers. Fig. 9(c) shows that the mobility of the region near hot spot is particularly obvious.

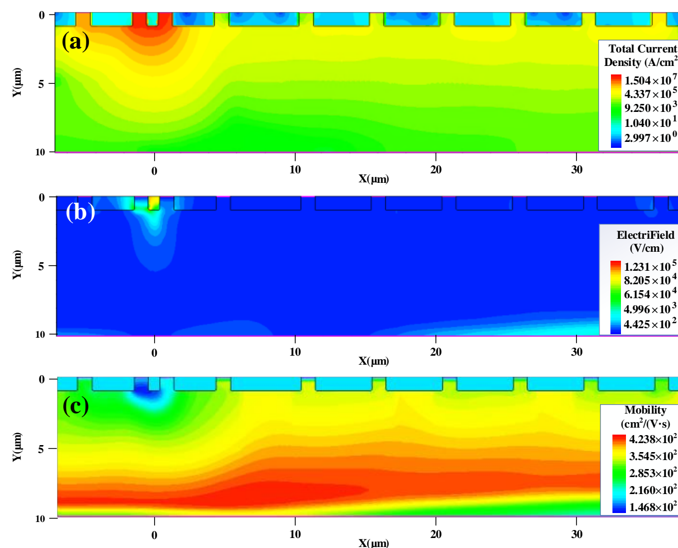

Fig. 9. The device of SCR1. (a)Total current density. (b) Electric field intensity. (c) Mobility distribution.

After the analysis of the previous section, when the pulse signal changes from negative to positive polarity, the signal of the input port has a positive voltage relative to the GND and the discharge path of the PS mode is turned on. So SCR2 will become the main path of current discharge, and a large amount of current will flow through the device SCR2 to cause its internal temperature to rise, as shown in Fig. 10.

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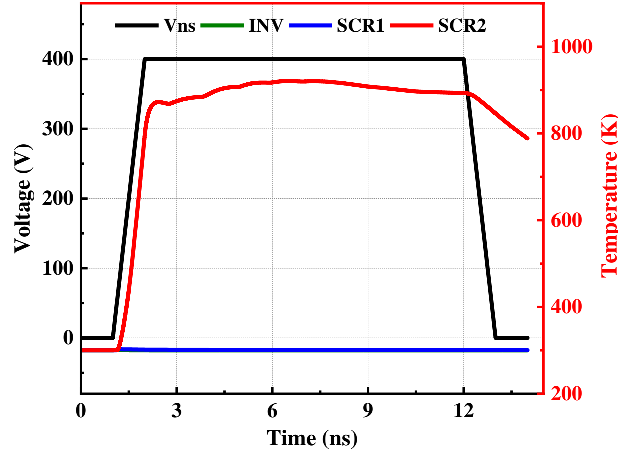

Fig.10. The variation of the peak temperature of the device with time under positive pulse.

A high temperature region appears inside the device SCR2 under positive polarity pulse, and obvious hot spots are observed, as shown in Fig. 11.

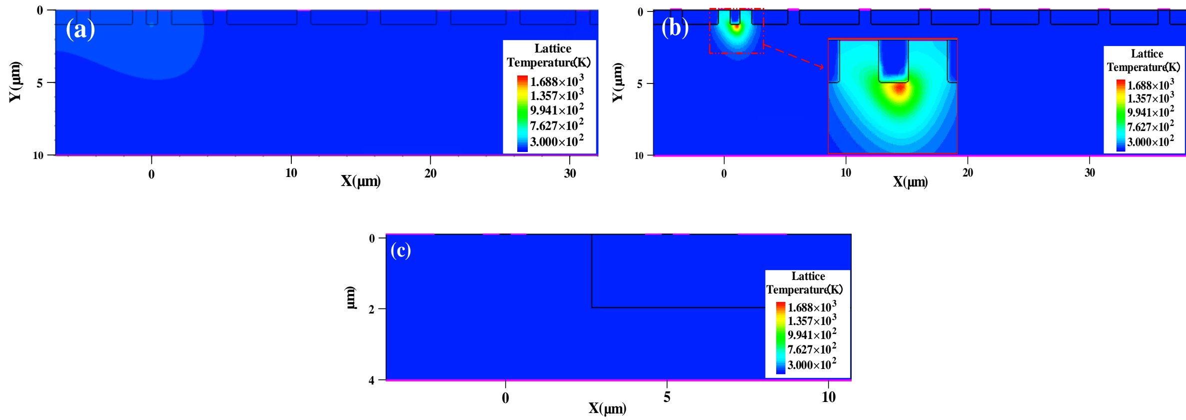

Fig. 11. Internal temperature distribution of the device under positive pulse. (a) Temperature distribution of SCR1. (b) Temperature distribution of SCR2. (c) Temperature distribution of CMOS inverter.

4. Influence of pulse parameters on device damage

In order to study the influence of pulse voltage signal parameters on the internal temperature of the device, the pulse signals with different voltage amplitudes and different rising edges are injected into the input port. In this paper, the internal peak temperature of the device reaches the melting point of the silicon material (1688K) as the thermal damage criterion of the device. If the EMP power injected into the device is high enough, the device may be partially burned during the pulse signal, resulting in irreversible physical damage, which further affects the circuit structure and function[29, 30]. In previous studies, it was found that SCR1 was easily burned during negative pulse injection, while SCR2 and CMOS inverters did not change significantly. Therefore, the influence of EMP signal parameters on SCR1 was mainly studied. Fig. 12 shows the relationship between the internal peak temperature of the device SCR1 and the pulse amplitude. The rising edge of the fixed injected EMP pulse is 2 ns.

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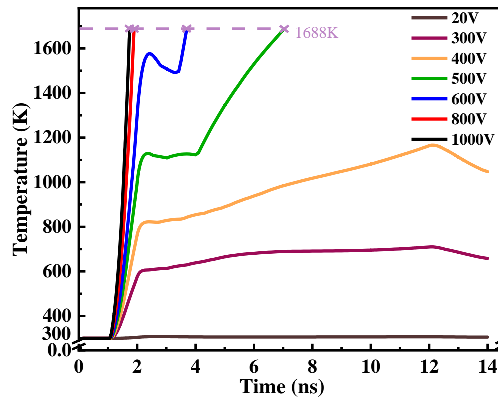

Fig. 12. The relationship between the peak temperature of the device and the pulse amplitude

When Vns = 20 V, the temperature of SCR1 is always maintained near 300 K, and the device is not damaged. With the increase of Vns to 400 V, the maximum temperature inside the device also failed to reach the melting point of the material during the pulse duration, and then the temperature of SCR1 decreased with the disappearance of the pulse, and it was determined that there was no damage. When the signal amplitude increases to 1000 V, the energy absorbed by the device increases in the same time, and the internal temperature continues to rise. Finally, the highest temperature of SCR1 reaches the melting point of the material, confirming its damage. On the other hand, when the amplitude of the injected pulse is fixed at 400 V, the relationship between the peak temperature inside the device and the rising edge of the pulse is extracted, as shown in Fig. 13.

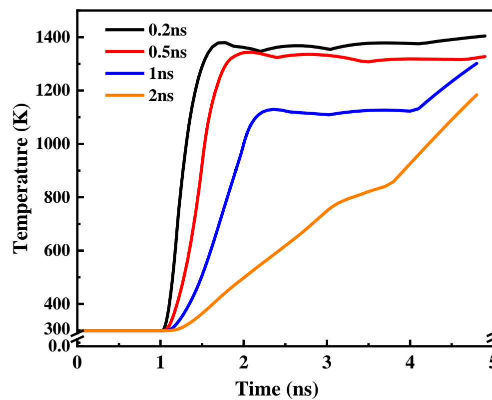

Fig. 13. The relationship between the peak temperature of the device and the rising edge

5. Conclusion

In this paper, a CMOS equivalent numerical model with ESD protection is proposed, and the EMP effect is investigated both electrically and thermally using a CMOS inverter as an entry point. By injecting pulse signals with positive and negative polarities into the ESD protection circuit and simulating based on TCAD, the port transient signals of the circuit model are extracted and the reasons for signals change are analyzed and summarized. The simulation results of the EMP pulse injection show that the device SCR1, which is connected to the VCC and the input “In”, has the risk of high-temperature damage under a negative pulse. And the device SCR2, which is located between the input and ground, is extremely susceptible to high-temperature damage under the injection of a positive pulse signal. Meanwhile, it is found that the vicinity of the two electrodes in the main SCR pathway of the device is a potential damage region by analyzing the temperature distribution map inside the device after the end of pulse injection. In addition, the relationships between the peak

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temperature and the amplitude and the rising edge of the pulse signal are obtained, respectively. By injecting microwave pulses with different power in the range of voltage amplitude from 20 V to 1000 V and rising edge from 0.2 ns to 2 ns into the input port of the ESD protection circuit, it is concluded that the higher the pulse signal power, the higher the peak temperature under a certain rising edge of the pulse signal. And it is also found that the peak temperature inside the device decreases with the increase of pulse rising edge under a certain power of the pulse signal.

These results indicate that there is a potential risk of damage to the ESD protection circuit module in CMOS circuits under the action of high-power electromagnetic pulse EMP. The simulation results and analyses in this paper fill the gap in the research on the microwave effect mechanism of ESD protection circuits, which can subsequently enhance the protection of the circuits under EMP pulses, and provide valuable references for the subsequent improvement of the reliability of the ESD protection circuits and prediction of the damage localization of the circuits.

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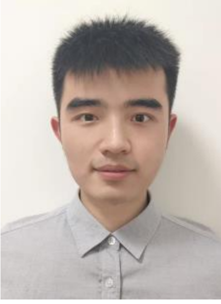

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